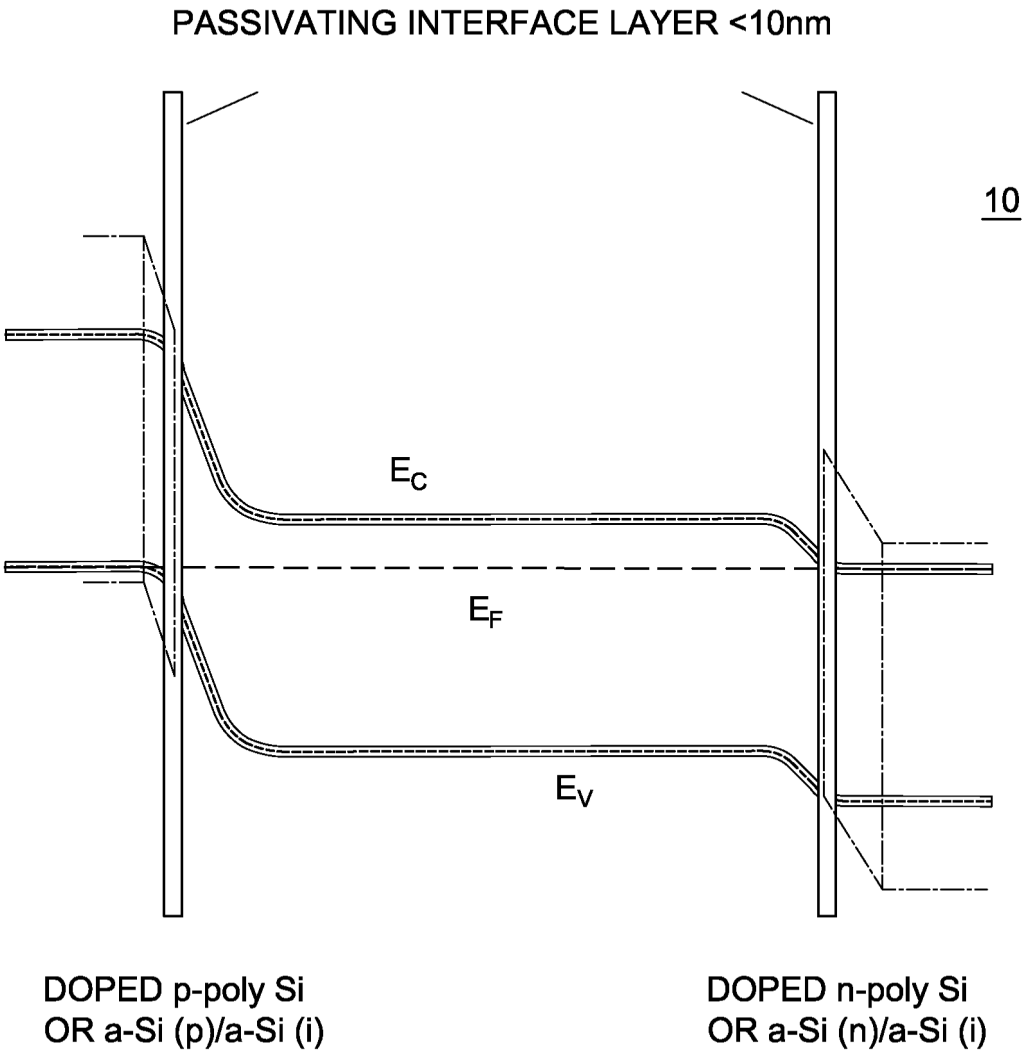

PASSIVATING INTERFACE LAYER <10nm
10
E_C
E_F
E_V
DOPED p-poly Si
OR a-Si (p)/a-Si (i)
DOPED n-poly Si
OR a-Si (n)/a-Si (i)

FIG. 1

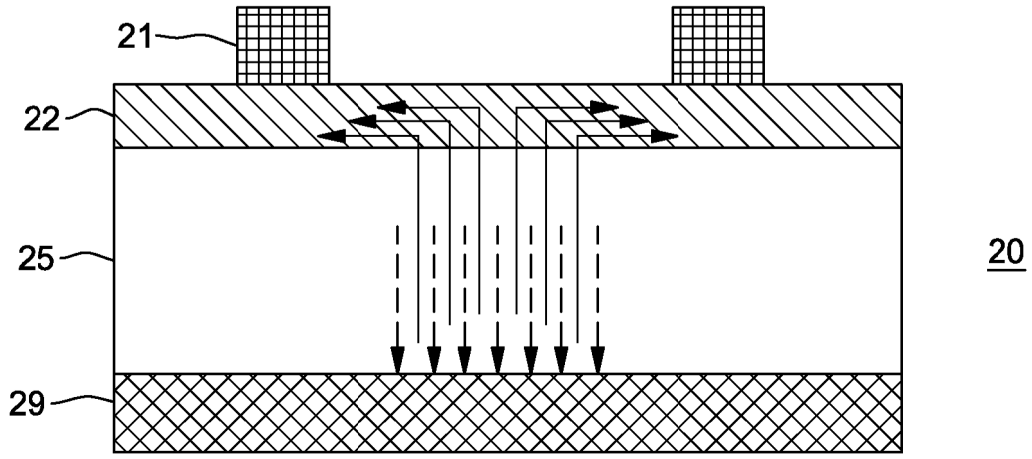


FIG. 2

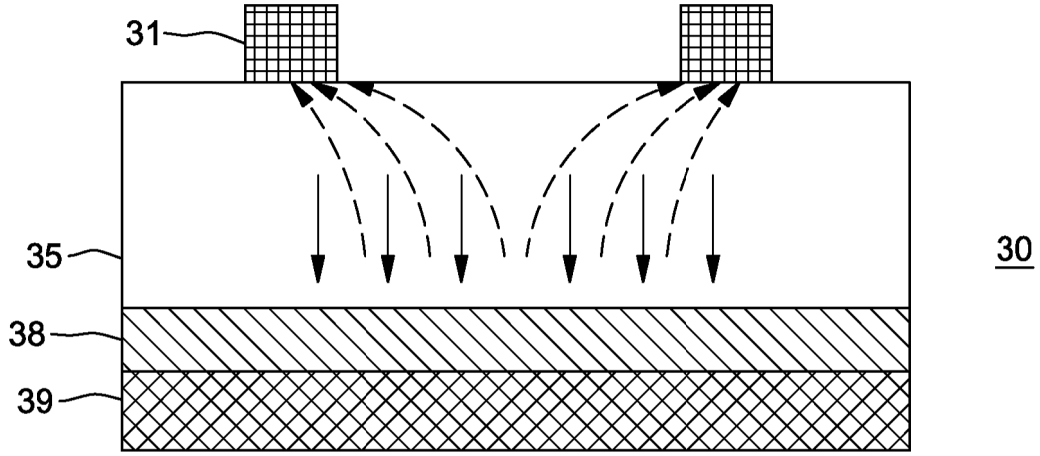


FIG. 3

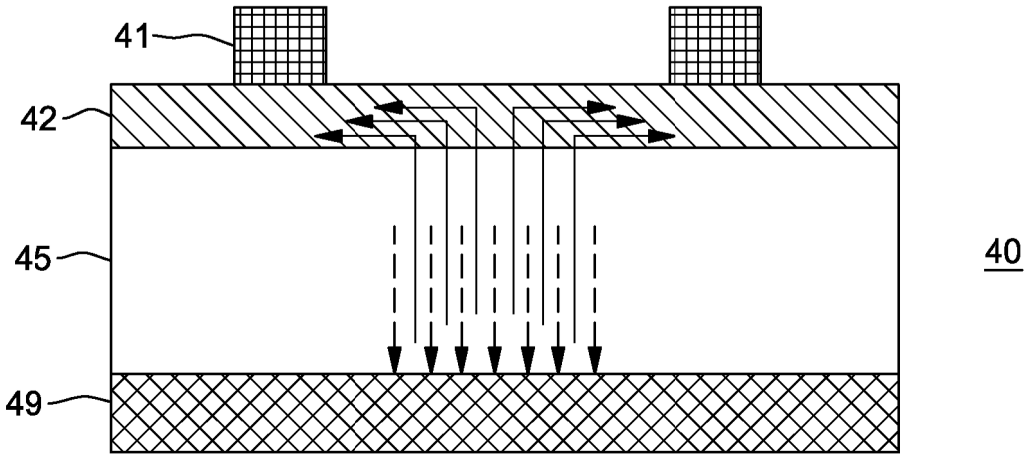


FIG. 4

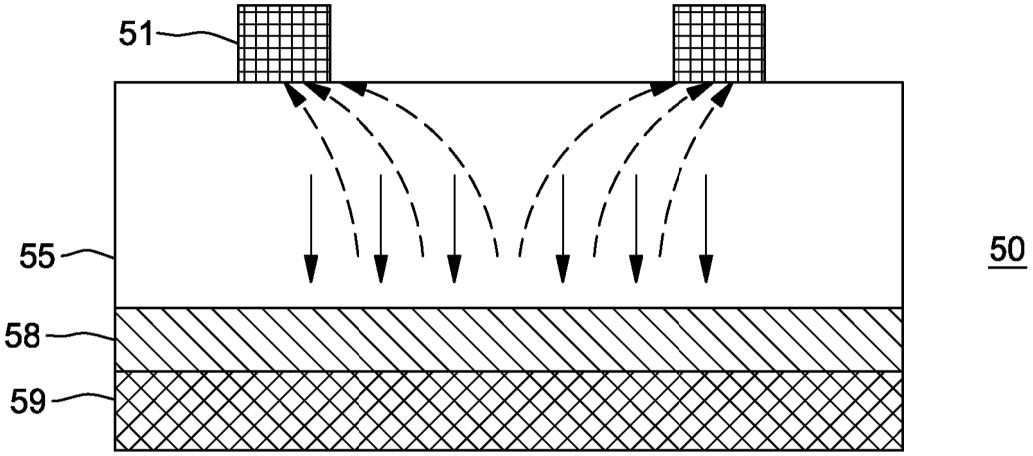


FIG. 5

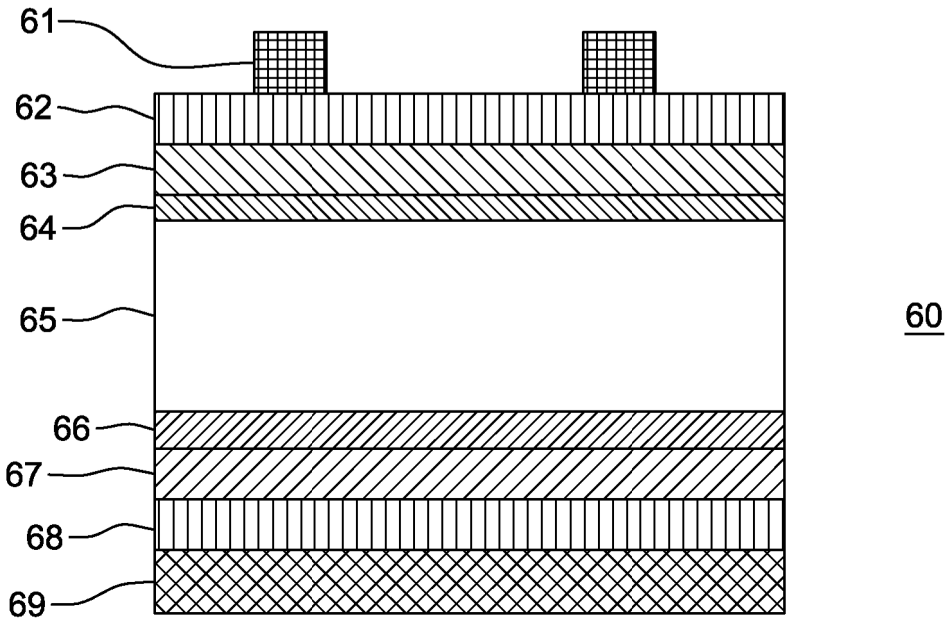


FIG. 6

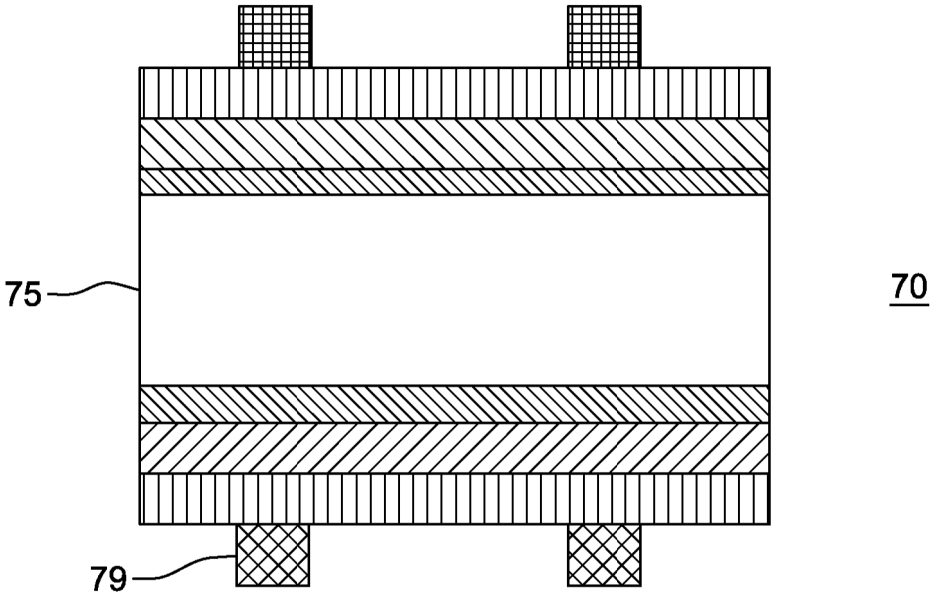


FIG. 7

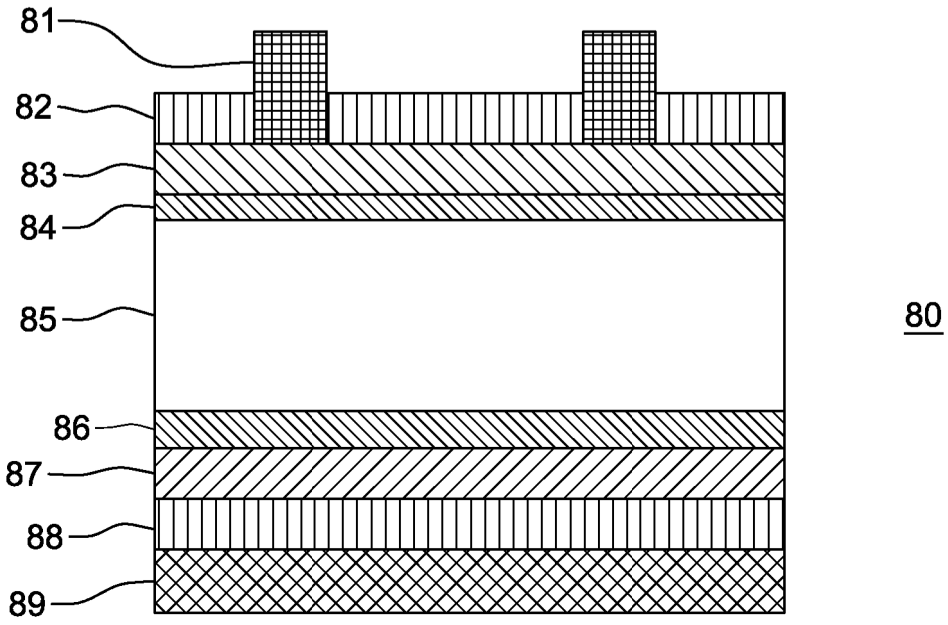


FIG. 8

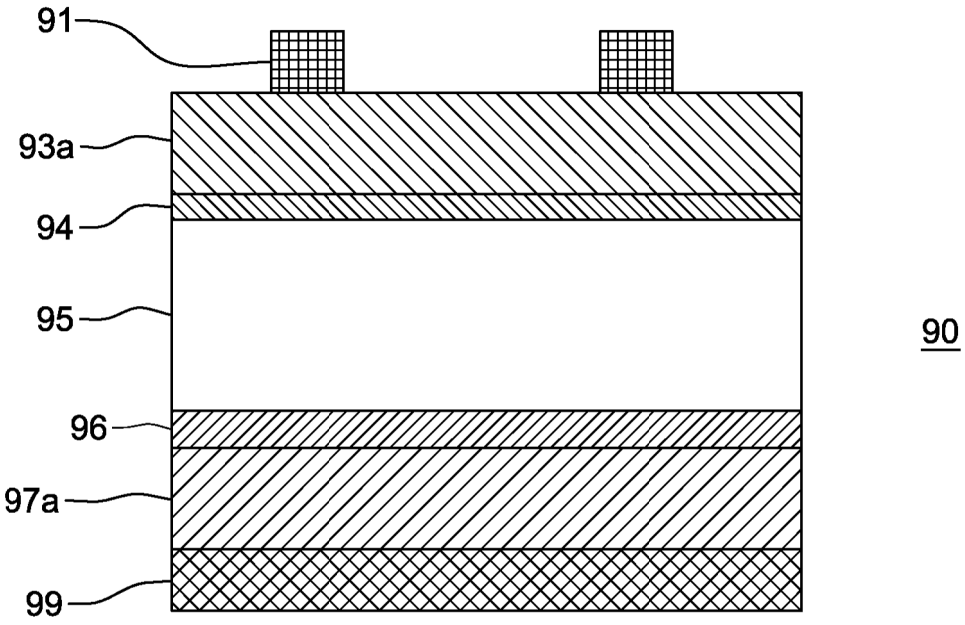


FIG. 9

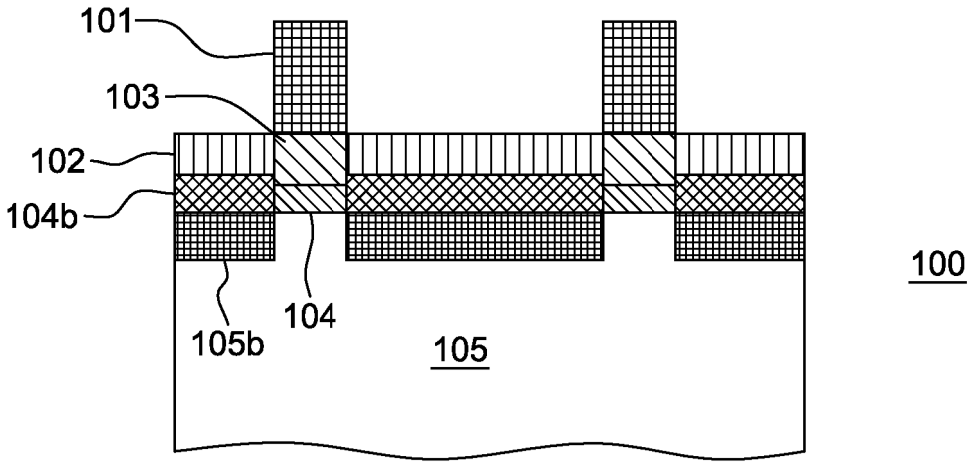


FIG. 10

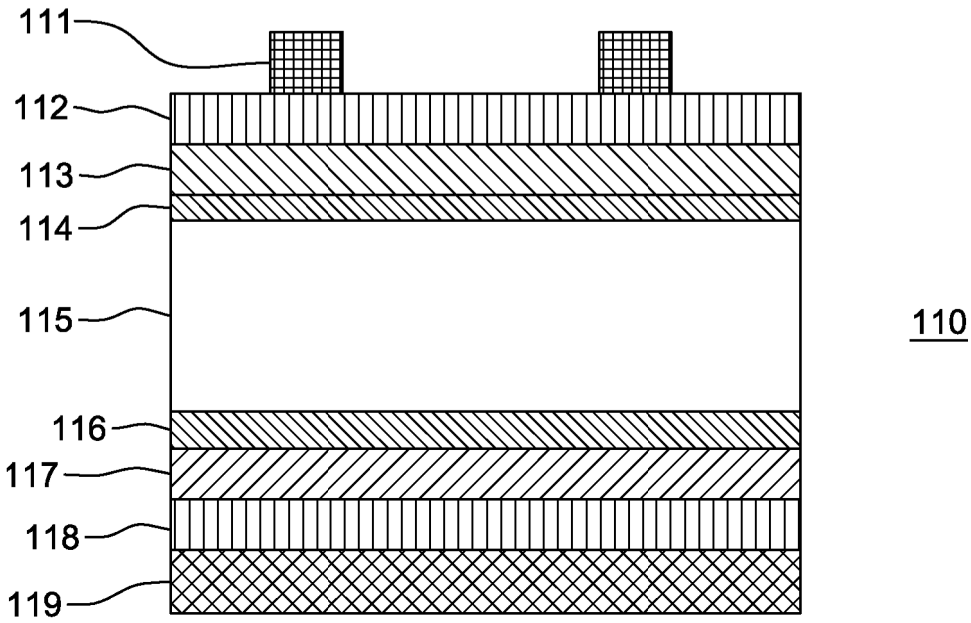


FIG. 11

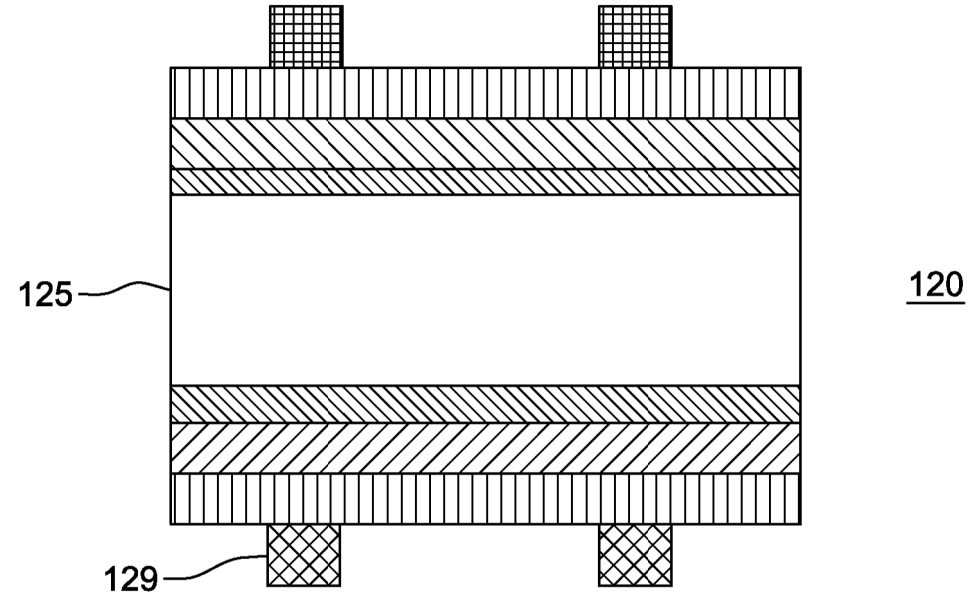


FIG. 12

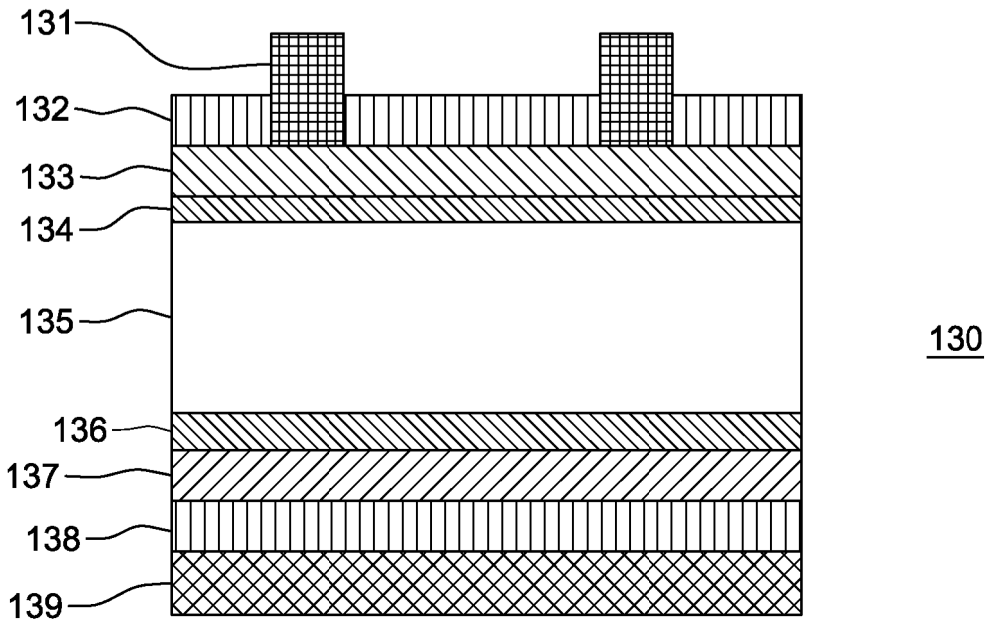

131
132
133
134
135
136
137
138
139
130

FIG. 13

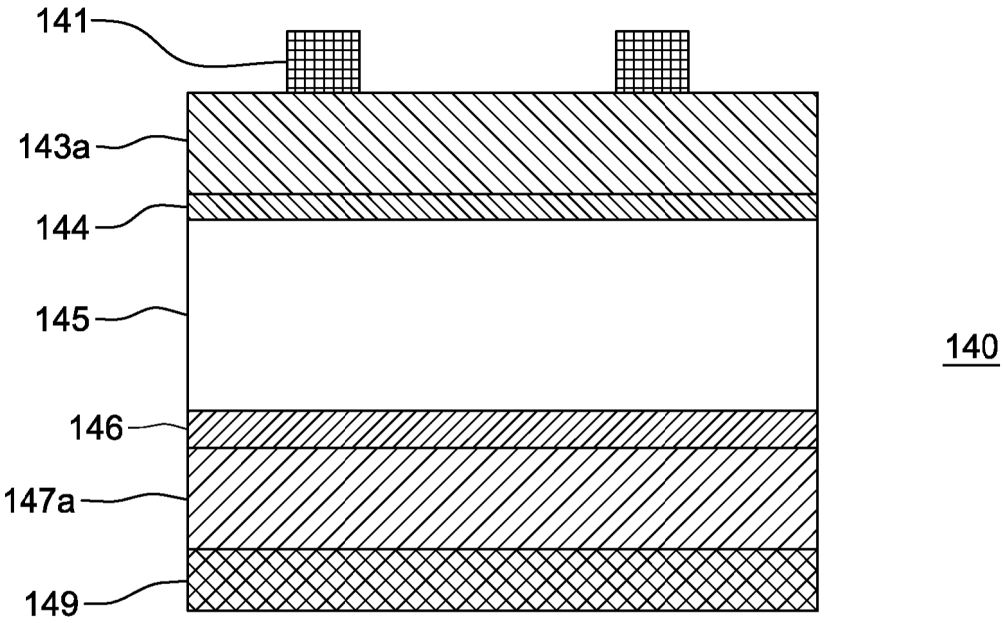

141
143a
144
145
146
147a
149
140

FIG. 14

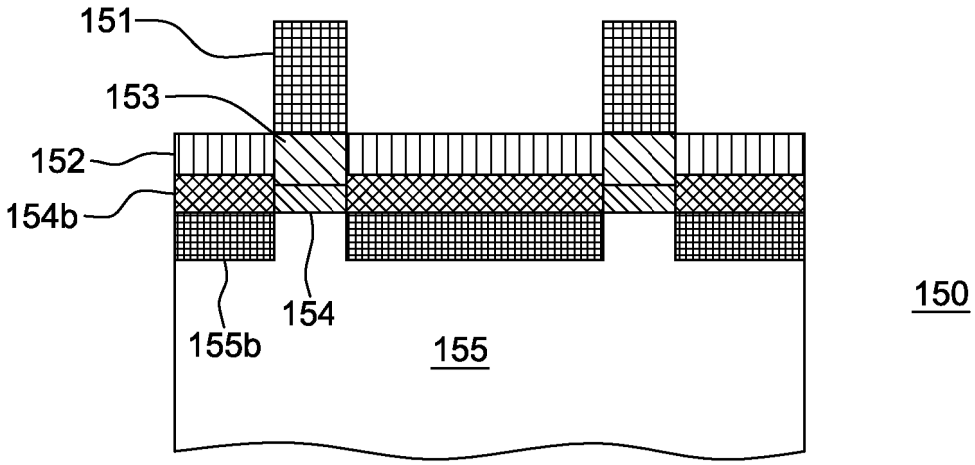


FIG. 15

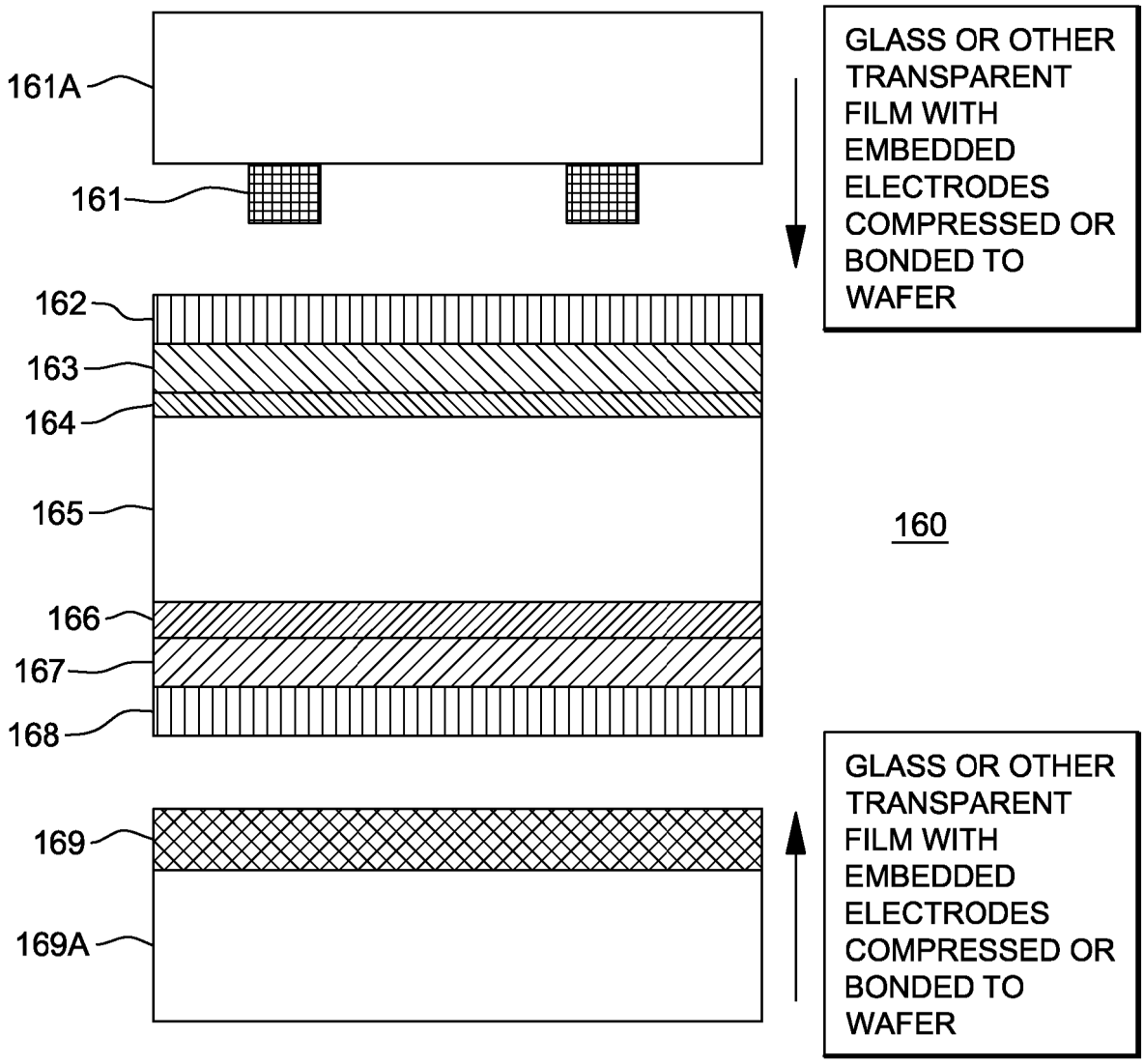

161A
161
162
163
164
165
166
167
168
169
169A
GLASS OR OTHER TRANSPARENT FILM WITH EMBEDDED ELECTRODES COMPRESSED OR BONDED TO WAFER
160
GLASS OR OTHER TRANSPARENT FILM WITH EMBEDDED ELECTRODES COMPRESSED OR BONDED TO WAFER

FIG. 16

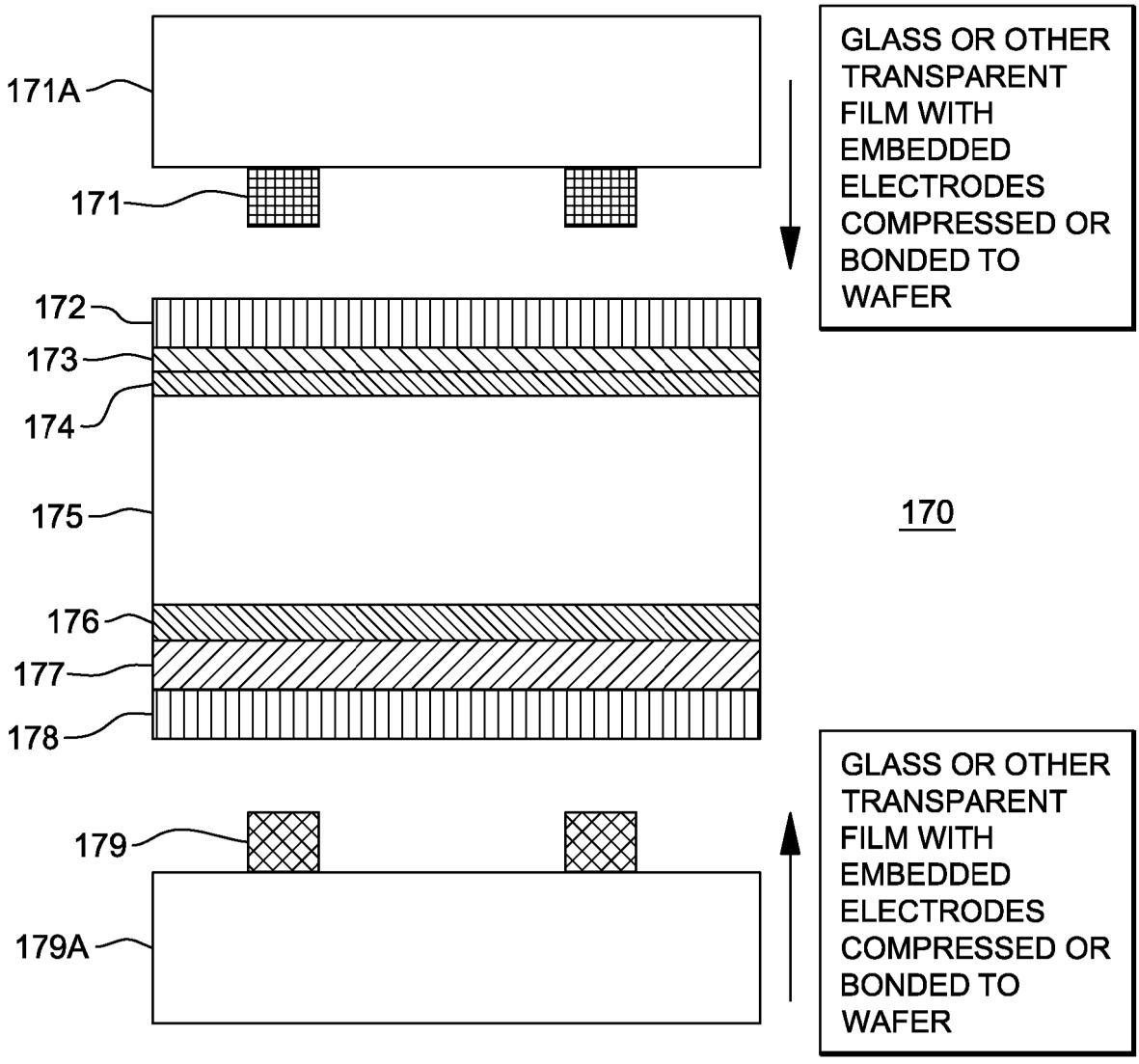

171A
171
GLASS OR OTHER TRANSPARENT FILM WITH EMBEDDED ELECTRODES COMPRESSED OR BONDED TO WAFER
172
173
174
175
170
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177
178
179
179A
GLASS OR OTHER TRANSPARENT FILM WITH EMBEDDED ELECTRODES COMPRESSED OR BONDED TO WAFER

FIG. 17

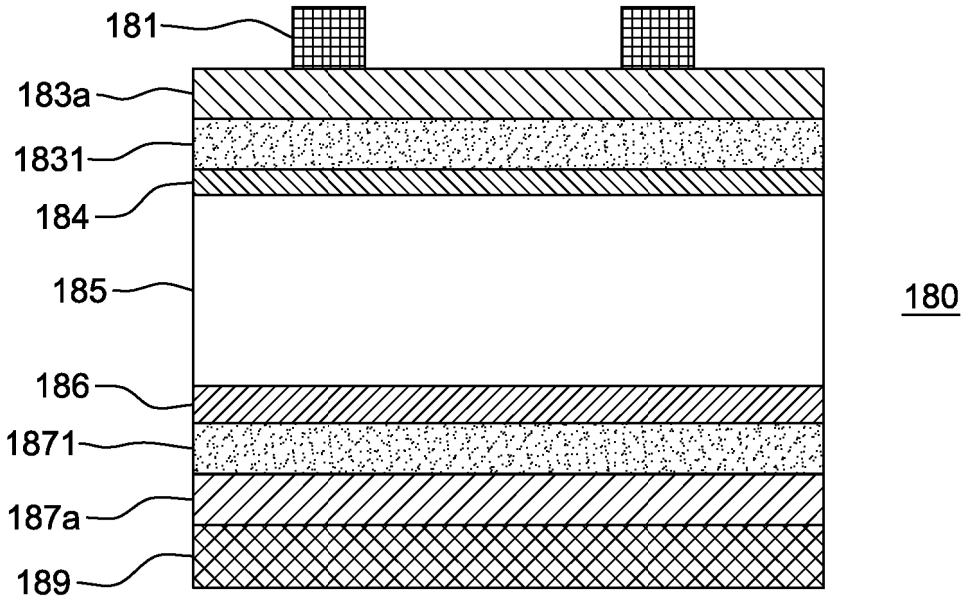


FIG. 18